

CD4030B Types

CMOS Quad Exclusive-OR Gate

High-Voltage Types (20-Volt Rating)

■ CD4030B types consist of four independent Exclusive-OR gates. The CD4030B provides the system designer with a means for direct implementation of the Exclusive-OR function.

The CD4030B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to V_{DD} +0.5V

DC INPUT CURRENT, ANY ONE INPUT ±10mA

POWER DISSIPATION PER PACKAGE (P_D):

For T_A = -55°C to +100°C 500mW

For T_A = +100°C to +125°C Derate Linearly at 12mW/°C to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package-Types) 100mW

OPERATING-TEMPERATURE RANGE (T_A) -55°C to +125°C

STORAGE TEMPERATURE RANGE (T_{stg}) -65°C to +150°C

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max +265°C

Features:

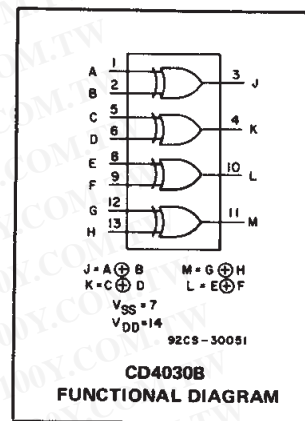
- Medium-speed operation—t_{pHL}, t_{pLH} = 65 ns (typ.) at V_{DD} = 10 V, C_L = 50 pF
- 100% tested for quiescent current at 20 V
- Standardized, symmetrical output characteristics
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package-temperature range):

1 V at V_{DD} = 5 V

2 V at V_{DD} = 10 V

2.5 V at V_{DD} = 15 V

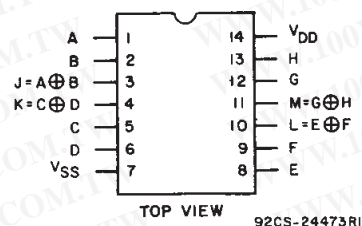
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



Applications:

- Even and odd-parity generators and checkers
- Logical comparators
- Adders/subtractors
- General logic functions

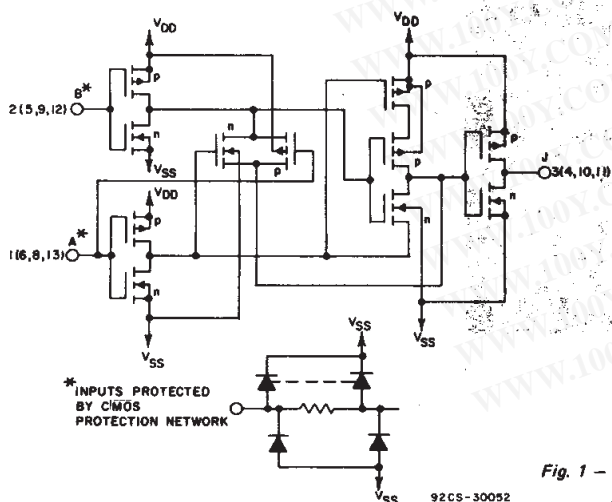
TERMINAL DIAGRAM Top View



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T _A = Full Package Temperature Range)	3	18	V



TRUTH TABLE FOR ONE OF FOUR IDENTICAL GATES

A	B	J
0	0	0
1	0	1
0	1	1
1	1	0

I = HIGH LEVEL
O = LOW LEVEL

Fig. 1 - Schematic diagram (1 of 4 identical gates).

勝特力材料 886-3-5753170
 胜特力电子(上海) 86-21-54151736
 胜特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

CD4030B Types

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	—	0.5	5	0.25	0.25	7.5	7.5	—	0.01	0.25	μA
	—	0.10	10	0.5	0.5	15	15	—	0.01	0.5	
	—	0.15	15	1	1	30	30	—	0.01	1	
	—	0.20	20	5	5	150	150	—	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0.10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0.15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I _{OH} Min.	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0.15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0.5	5	0.05				—	0	0.05	V
	—	0.10	10	0.05				—	0	0.05	
	—	0.15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0.5	5	4.95				4.95	5	—	V
	—	0.10	10	9.95				9.95	10	—	
	—	0.15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	0.5, 4.5	—	5	1.5				—	—	1.5	V
	1.9	—	10	3				—	—	3	
	1.5, 13.5	—	15	4				—	—	4	
Input High Voltage, V _{IH} Min.	0.5, 4.5	—	5	3.5				3.5	—	—	V
	1.9	—	10	7				7	—	—	
	1.5, 13.5	—	15	11				11	—	—	
Input Current I _{IN} Max.	—	0.18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA

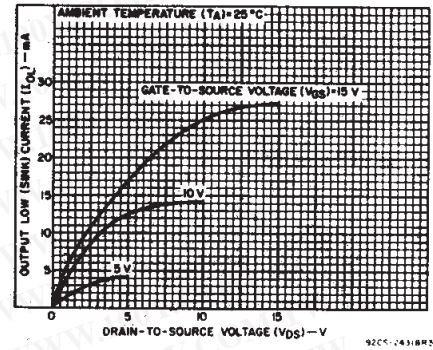


Fig. 2 – Typical output low (sink) current characteristics.

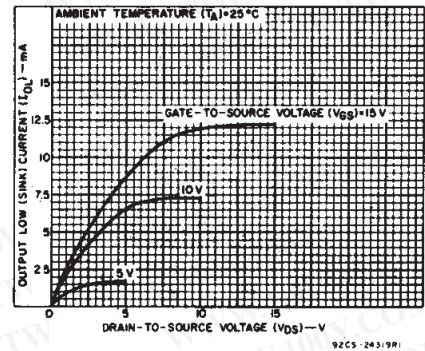


Fig. 3 – Minimum output low (sink) current characteristics.

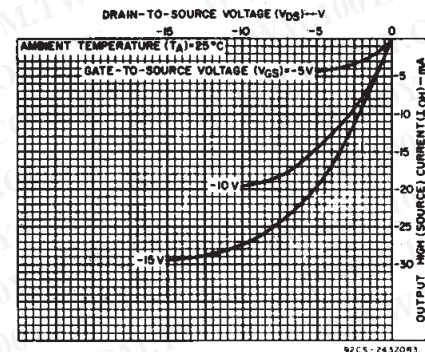


Fig. 4 – Typical output high (source) current characteristics.

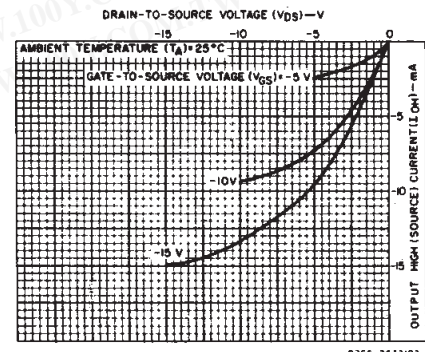


Fig. 5 – Minimum output high (source) current characteristics.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 KΩ

CHARACTERISTIC	CONDITIONS	LIMITS		UNITS	
		V _{DD} (V)	LIMITS		
			Typ.		Max.
Propagation Delay Time, t _{PLH} , t _{PHL}	Any Input	5	140	280	ns
		10	65	130	
		15	50	100	
Transition Time, t _{THL} , t _{TLH}	Any Input	5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C _{IN}	Any Input	5	7.5	pF	

3
 COMMERCIAL CMOS
 HIGH VOLTAGE ICs

CD4030B Types

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw

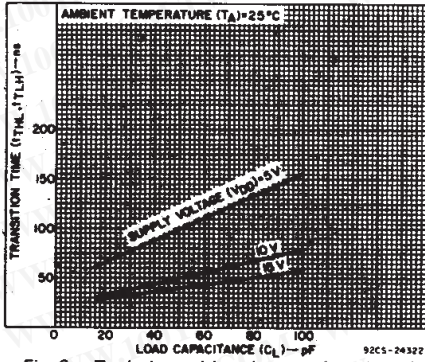


Fig. 6 - Typical transition time as a function of load capacitance.

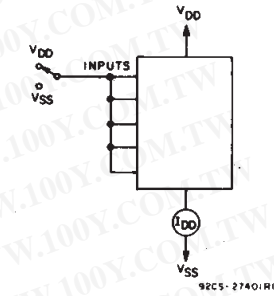


Fig. 10 - Quiescent-device current test circuit.

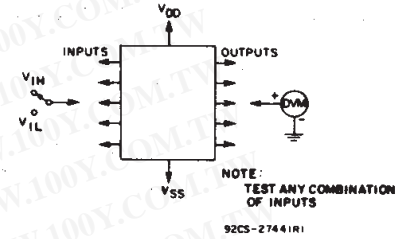


Fig. 11 - Input-voltage test circuit.

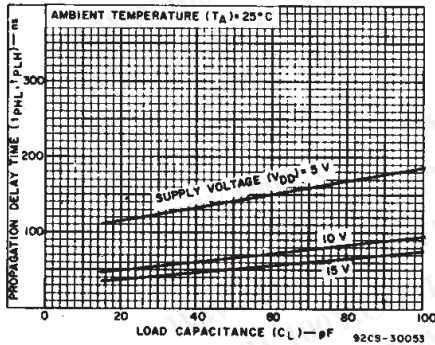


Fig. 7 - Typical propagation delay time as a function of load capacitance.

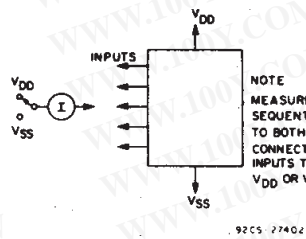


Fig. 12 - Input-current test circuit.

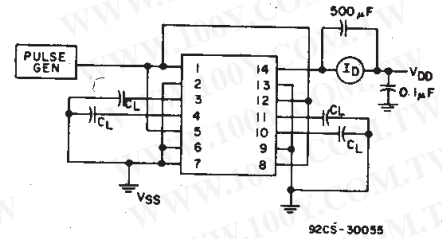


Fig. 13 - Dynamic power dissipation test circuit.

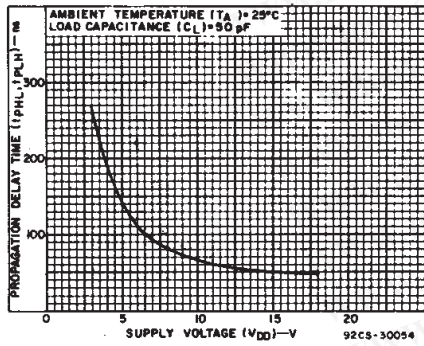


Fig. 8 - Typical propagation delay time as a function of supply voltage.

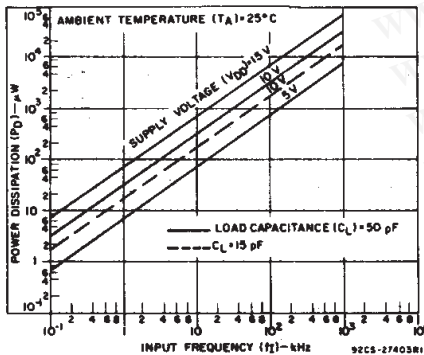
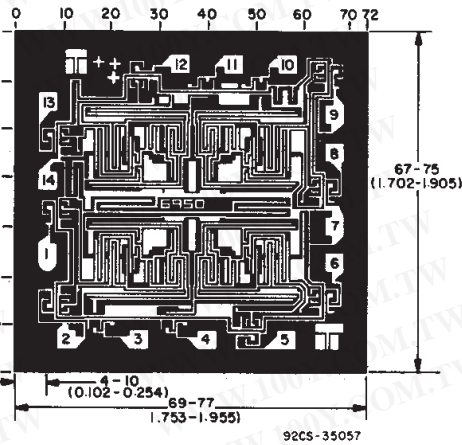


Fig. 9 - Typical dynamic power dissipation as a function of input frequency.



Dimensions and pad layout for CD4030BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.